

RJK0353DPA

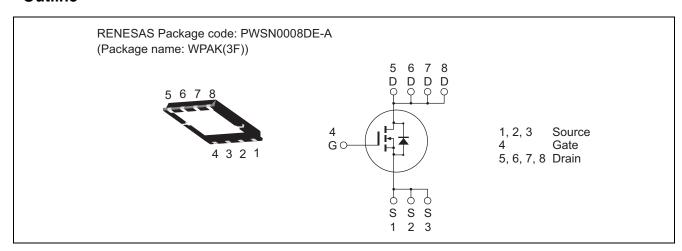
30V, 35A, $5.2m\Omega$ max. N Channel Power MOS FET High Speed Power Switching

R07DS0915EJ0500 Rev.5.00 Mar 19, 2013

Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
- Pb-free
- Halogen-free

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I _D	35	Α
Drain peak current	I _{D(pulse)} Note1	140	А
Body-drain diode reverse drain current	I _{DR}	35	А
Avalanche current	I _{AP} Note 2	16	А
Avalanche energy	E _{AR} Note 2	25.6	mJ
Channel dissipation	Pch Note3	40	W
Channel to Case Thermal Resistance	θch-C	3.13	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tch = 25°C, Rg \geq 50 Ω
- 3. $Tc = 25^{\circ}C$

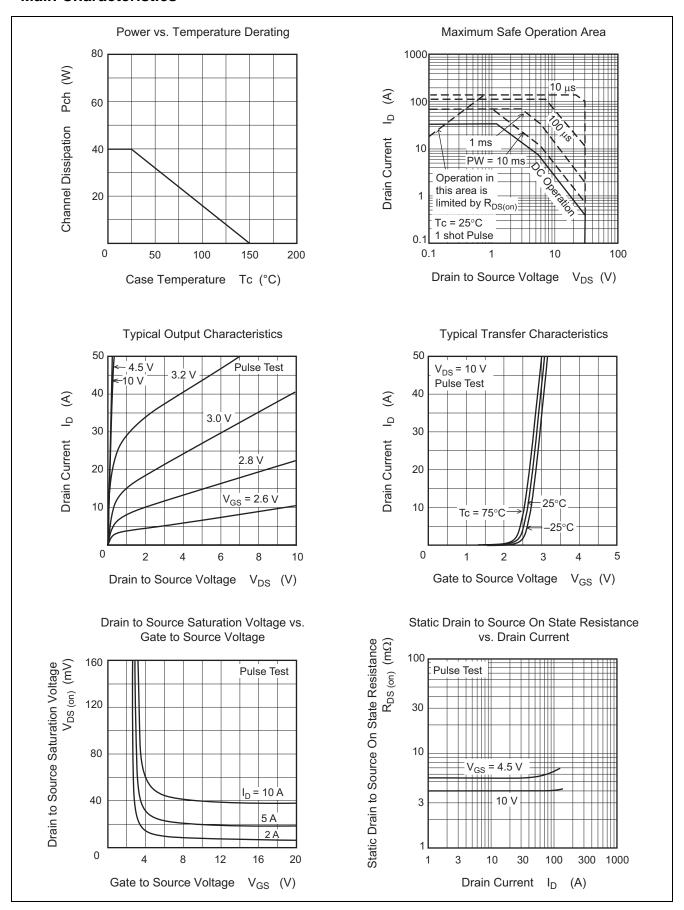
Electrical Characteristics

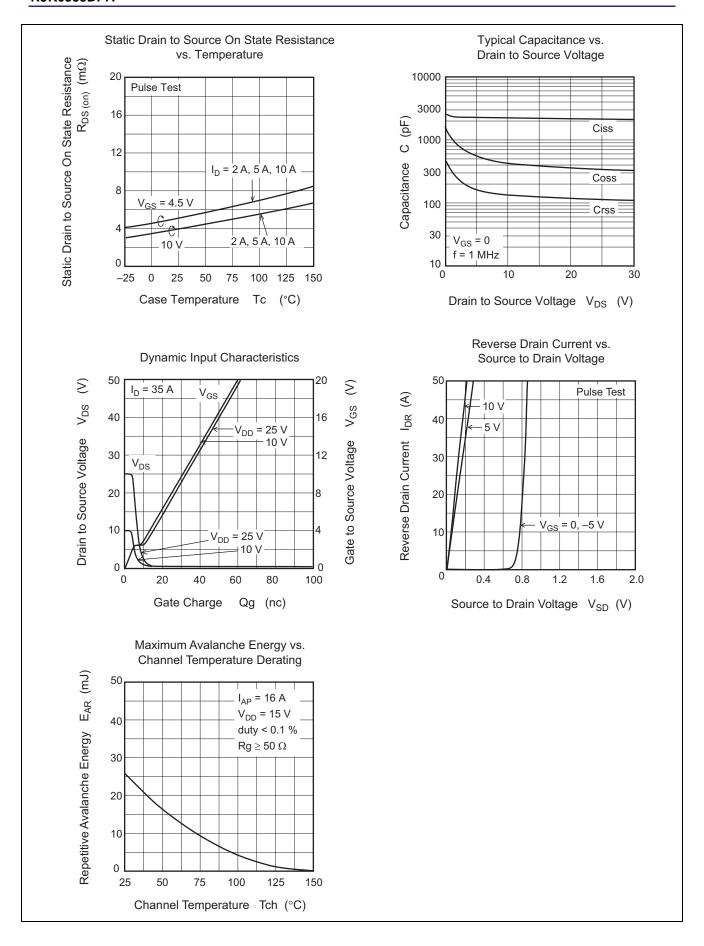
 $(Ta = 25^{\circ}C)$

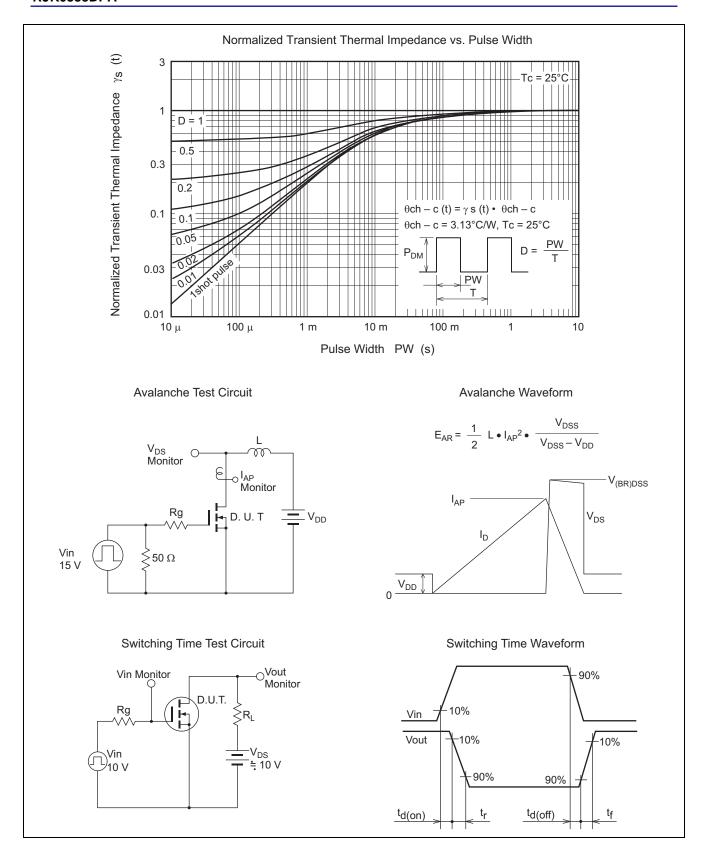
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	1	μА	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	1.2	_	2.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}	_	4.0	5.2	mΩ	$I_D = 17.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance	R _{DS(on)}	_	5.4	7.6	mΩ	$I_D = 17.5 \text{ A}, V_{GS} = 4.5 \text{ V}^{Note4}$
Forward transfer admittance	y _{fs}	_	70	_	S	$I_D = 17.5 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	2180	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	420	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	135	_	pF	
Gate Resistance	Rg	_	2.0	_	Ω	
Total gate charge	Qg	_	14	_	nC	$V_{DD} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$
Gate to source charge	Qgs	_	6.0	_	nC	I _D = 35 A
Gate to drain charge	Qgd	_	3.0	_	nC	
Turn-on delay time	t _{d(on)}	_	8.5	_	ns	$V_{GS} = 10 \text{ V}, I_D = 17.5 \text{ A},$
Rise time	t _r	_	4.8	_	ns	$V_{DD} \cong 10 \text{ V}, R_L = 0.57 \Omega,$
Turn-off delay time	t _{d(off)}	_	47.5	_	ns	$Rg = 4.7 \Omega$
Fall time	t _f	_	6.0	_	ns]
Body-drain diode forward voltage	V_{DF}	_	0.83	1.08	V	$I_F = 35 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t _{rr}	_	25	_	ns	$I_F = 35 \text{ A}, V_{GS} = 0$ $di_F / dt = 100 \text{ A} / \mu \text{s}$

Notes: 4. Pulse test

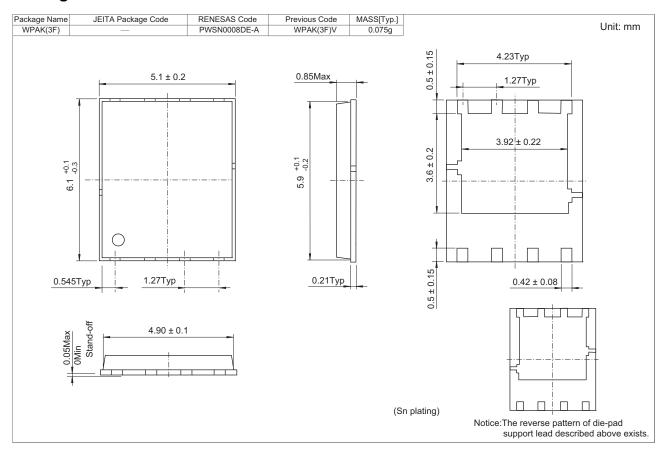
Main Characteristics







Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container
RJK0353DPA-01-J0B	2500 pcs	Taping

Note: The symbol of 2nd "-" is occasionally presented as "#".

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